PNP/NPN Epitaxial Planar Silicon Darlington Transistors



## 2SB1224/2SD1826

# **Driver Applications**

## **Applications**

 Suitable for use in control of motor drivers, printer hammer drivers, relay drivers, and constant-voltage regulators.

#### **Features**

- · High DC current gain.
- · Large current capacity and wide ASO.
- · Micaless package facilitaing mounting.

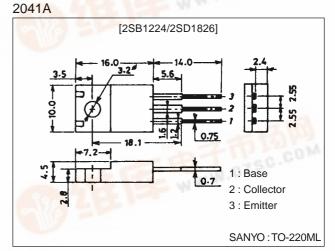
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## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

## **Package Dimensions**

unit:mm



Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>СВО</sub>		(-)70	V
Collector-to-Emitter Voltage	VCEO		(-)60	V
Emitter-to-Base Voltage	VEBO		(-)6	V
Collector Current	lС		(-)7	Α
Collector Current (Pulse)	I <sub>CP</sub>	1 to	(–)10	Α
Collector Dissipation	PC	AND AND LOS W	2.0	W
		Tc=25°C	25	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg	- 0.34	-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0			(–)0.1	mA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)5V, I <sub>C</sub> =0			(-)3.0	mA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)3.5A	2000	5000		101
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)3.5A		20	5 U	MHz
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)3.5A, I <sub>B</sub> =(-)7mA	W III	0.9	(–)1.5	V
				(-1.0)		V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)3.5A, I <sub>B</sub> =(-)7mA			(-)2.0	V

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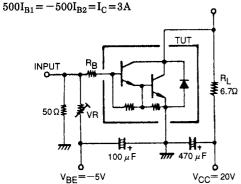
SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	] UIIII
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)5mA, I <sub>E</sub> =0	(–)70			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(-)50mA, R <sub>BE</sub> =∞	(–)60			V
Turn-ON Time	ton	See specified Test Circuit		0.6		μs
				(0.5)		μs
Storage Time	t <sub>stg</sub>	See specified Test Circuit		3.0		μs
				(1.5)		μs
Fall Time	t <sub>f</sub>	See specified Test Circuit		1.7		μs
				(1.4)		μs

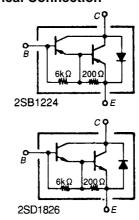
#### **Switching Time Test Circuit**

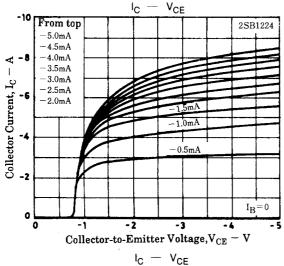
#### PW = 50 $\mu$ s, Duty cycle $\leq 1\%$ 500I<sub>R1</sub> = -500I<sub>R2</sub> = I<sub>C</sub> = 3A

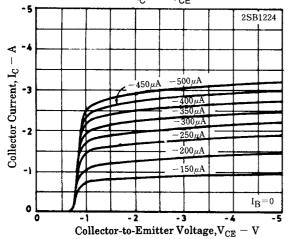


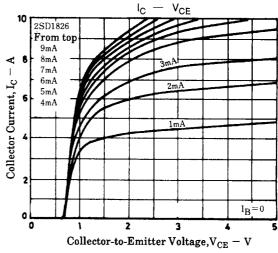
(For PNP, the polarity is reversed.)

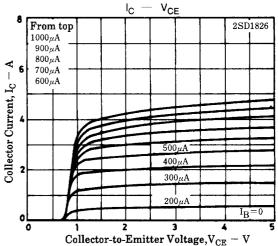
#### **Electrical Connection**



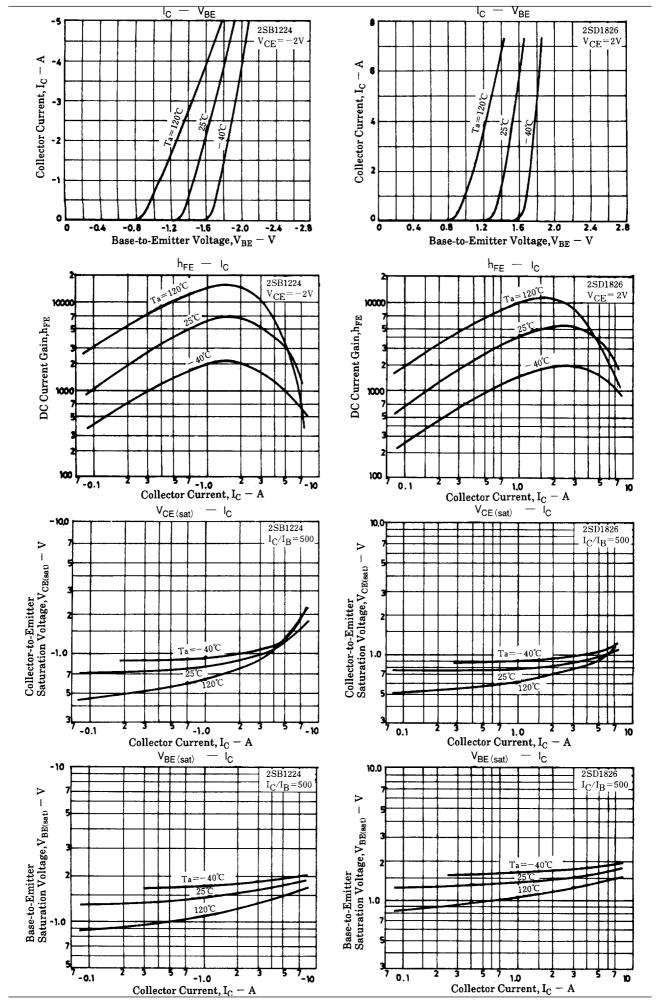




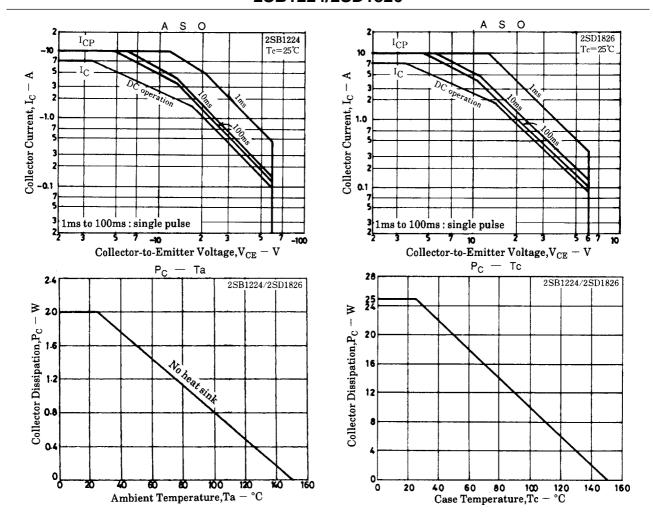




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